

Notice of References CitedApplication/Control No.
09/902,518Applicant(s)/Patent Under
Reexamination
HUANG ET AL.Examiner
Michael S. LebentrittArt Unit
2824

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★		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.